



(51) International Patent Classification:
H01L 21/78 (2006.01) *B23K 26/36* (2006.01)

(21) International Application Number:
PCT/US2010/028888

(22) International Filing Date:
26 March 2010 (26.03.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/413,068 27 March 2009 (27.03.2009) US

(71) Applicant (for all designated States except US): **ELECTRO SCIENTIFIC INDUSTRIES, INC.** [US/US]; 13900 NW Science Park Drive, Portland, Oregon 97229 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **PIROGOVSKY, Peter** [US/US]; 8815 SW 45th Drive, Portland, Oregon 97219 (US). **ALBELO, Jeffrey** [US/US]; 9045 SE Au-

gustine Court, Portland, Oregon 97086 (US). **O'BRIEN, James** [US/US]; 912 NE Revere Avenue, Unit 1, Bend, Oregon 97701 (US). **OSAKO, Yasu** [JP/US]; 14057 Chelsea Drive, Lake Oswego, Oregon 97035 (US).

(74) Agent: **LEONARD, Patrick**; Electro Scientific Industries, Inc., 13900 NW Science Park Drive, Portland, Oregon 97229 (US).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG,

[Continued on next page]

(54) Title: METHOD FOR LASER SINGULATION OF CHIP SCALE PACKAGES ON GLASS SUBSTRATES

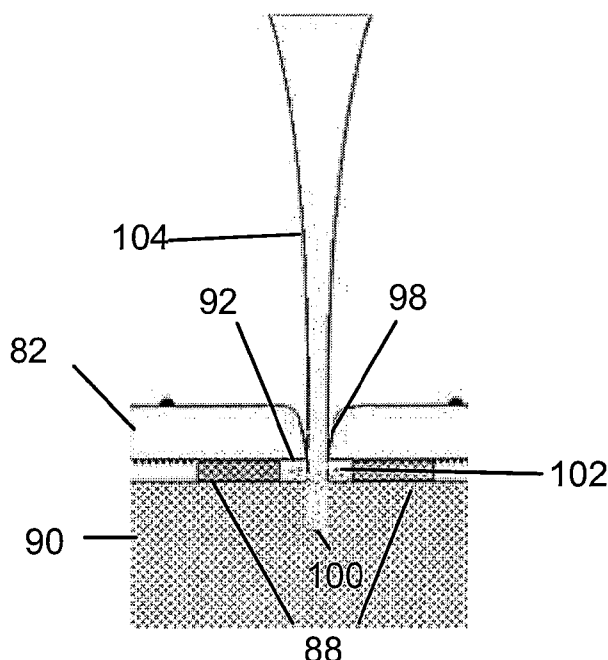


Fig 7a

(57) Abstract: An improved method for singulation of compound electronic devices is presented. Compound electronic devices are manufactured by combining two or more substrates 84, 90 into an assembly 10 containing multiple devices 12. Presented are methods for singulation of compound electronic devices 12 using laser processing 80. The methods presented provide fewer defects such as cracking 58 or chipping 39 of the substrates 36, 50 while minimizing the width of the kerf 142 and maintaining system throughput.



ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *without international search report and to be republished upon receipt of that report (Rule 48.2(g))*

METHOD FOR LASER SINGULATION OF CHIP SCALE PACKAGES ON GLASS SUBSTRATES

Technical Field

[0001] The present invention relates to singulation of electronic devices. In particular it relates to singulation of compound electronic devices, where the devices are constructed by assembling layers of potentially dissimilar substrates. In more particular it relates to singulation of image sensor compound semiconductor devices that comprise a substrate or wafer, often silicon, containing active circuit elements combined with an optically transparent protective substrate, often glass or sapphire.

Background

[0002] Semiconductor and other electronic devices are typically manufactured by creating multiple copies of a device together on a substrate and then singulating the devices. Substrates can be comprised of silicon, sapphire, ceramic, glass or glass-like material. Singulation is the act of separating multiple devices manufactured on a substrate from each other by creating a cut or break between the devices to form individual devices. Singulation can be performed in many ways. One, called scribing, is accomplished by first machining a cut or trench in the surface of the substrate or material attached to the surface of the substrate without cutting through the substrate. This is followed by mechanically breaking or cleaving the substrate to separate the die. This cut or trench can be formed by mechanical sawing, chemical etching, laser radiation or a combination. Another way to singulate substrates is called dicing, where the entire depth of the desired separation is performed by mechanical sawing, chemical etching or laser radiation or a combination, without mechanical cleaving.

[0003] Semiconductor devices are typically arranged in rows and columns on a substrate, with areas free from critical components between them. These free areas are called “streets” and typically form two sets of straight lines arranged perpendicularly to each other in order to yield rectangular devices once singulated. Fig 1 shows a typical

semiconductor wafer 10 comprised of compound devices, one of which is indicated 12 and streets, one of which is indicated 14. Also shown is top surface metal, one of which is indicated 16.

[0004] Semiconductor devices are becoming more complex as consumer's desires for more functions in smaller and smaller packages are encouraging manufacturers to put more circuitry into less volume. Three trends emerge from this increase in packaging density. First, substrates are getting thinner, making them more susceptible to damage from cracks or chips. Second, circuit density is getting greater and as substrate space becomes more valuable, there is a desire to minimize the area devoted to streets. Finally, electronic devices are increasingly packaged as compound devices wherein multiple substrates are assembled prior to singulation in order to take advantage of the parallelism inherent in wafer scale integration and package more capability into a smaller volume or to protect underlying components.

[0005] Compound semiconductor devices can be made of multiple substrates, possibly containing multiple semiconductor devices, assembled into a single functional device. These compound devices are often assembled prior to device singulation and can present problems for typical singulation methods. Figure 2 shows an exemplary compound device, in this case a complementary metal-oxide semiconductor (CMOS) image sensor, from a side view, showing a silicon wafer 20 containing active circuit elements (not shown), solder bumps, one of which is indicated 22, and top surface metal, one of which is indicated 24. The wafer 20 is separated from the glass cover plate 26 by shims, one of which is indicated 28. One of the streets is indicated 30, as the region between the adjacent dotted lines. In this device, the image sensor is on the surface of the silicon wafer 20 that faces the glass cover plate 26. The transparent cover plate protects the sensor while allowing light to reach the sensor.

[0006] One prior art process for singulating semiconductor devices is to cut the wafers with a mechanical saw, for example the DISCO DAD3350 (DISCO Corporation, Tokyo, Japan). One of the disadvantages of mechanical saws is they can cause chipping and cracking along the kerf or cut they create. These chips and cracks weaken the substrate and can cause problems with the eventual semiconductor device. This weakening of substrates due to chipping and cracking becomes worse as substrates become thinner.

Mechanical saws also have a minimum kerf size based on the minimum size of the saw. This limits the manufacturer's ability to reduce street size and improve the usable area of the substrate. One possible solution to the cracking problem is to slow down the rate at which the saw moves through the substrate. Careful adjustment of cutting pressure and speed of the saw through the material is required to avoid creating cracks, both of which cause decreases in throughput, since less pressure means more passes with a mechanical saw and slower speed required more time per pass. While this can reduce the cracking and chipping problems, it can slow down the singulation process unacceptably.

[0007] An alternative process for singulating semiconductor devices is to use a chemical or plasma etching to form the cuts. An example of this is shown in US patent 6,573,156, assigned to OMM, (OMM, Inc., San Diego, CA). In this process a trench is etched on one side of a wafer, a temporary holding material is applied to that side and the opposite side is then etched. The temporary holding material is then removed to permit the individual semiconductor devices to be separated. This method has the disadvantage of requiring several additional steps and additional equipment to be added to the manufacturing process, thereby increasing manufacturing cost and time.

[0008] Another common method of making the cuts is with a laser beam. Laser beams are also capable of making non-straight cuts in cases where device outlines or streets are not straight or perpendicular. Singulation can be accomplished by using a laser beam to machine completely through the substrate forming a through-cut, thereby separating the devices (dicing), or by making a scribe or partial cut into the substrate, which is subsequently mechanically cleaved or fractured from the bottom of the scribe to the opposite surface of the substrate (scribing). Singulating semiconductor devices with a laser beam can reduce the substrate area devoted to streets, since the laser beam can machine a kerf smaller than the smallest saw blade. The laser beam is capable of either cutting a kerf or creating a scribe in the materials that typically make up compound semiconductor devices such as silicon wafers and glass cover plates. These kerfs or scribes can be smaller than the 100 microns typically made by mechanical saws. Figure 3 shows a glass substrate after being scribed with nanosecond laser beam pulses. In this case a pulsed, frequency doubled Nd:YAG laser is used to direct laser pulses at a glass substrate to form scribes. The laser operates at 532 nm, emitting pulses with a temporal

[0009] Another problem with scribing or cutting glass with nanosecond-scale laser pulses is the creation of cracks. Fig 4a shows a cross-sectional view of a laser scribe in a glass substrate 50 scribed with the same laser parameters as the scribes in Figs 3 and 4. This image clearly shows the heat affected zone (HAZ) 52 surrounding the scribe 54. In addition, a void 56 and stress fractures 58 are shown near the bottom of the scribe 54. These defects, likely caused by thermal effects from the nanoseconds long laser pulses, will cause cracks when the glass substrate is cleaved following scribing as shown in Fig 4b. Fig 4b shows a side view of the substrate 50 from Fig 4a following cleaving, with the scribe 54 on the right and representative cracks 60 shown propagating from the area of the scribe 54. These cracks 60 are a result of cleaving the substrate 50 in the presence of voids and stress fractures as exemplified in Fig 4a 56, 58. Following packaging, cracks such as these can potentially propagate, causing device failure. Mechanical saws can also create this type of crack.

[0010] A process designed to overcome this chipping and cracking is to use a chemical or plasma etchant to “melt” the edges to attempt to remove the effects of the mechanical saw. An example of this is described in US patent application 2006/0249480 Laser Machining Using an Active Assist Gas. In this application, a process of using a halogen assist gas to help reduce chipping and cracking from resulting from laser machining substrates is shown. This application indicates an increase in die strength by reducing chipping and cracking, but at the cost of the additional equipment required to safely deliver and exhaust caustic gas to and from the work area.

[0011] Compound devices present additional problems when singulated by existing methods. In the case of mechanical saws, the saw would have to cut through the street 30 between the dotted lines in Fig 2, through both the silicon wafer 20 and the glass cover

plate 26. A particular problem with compound devices is the quality of the kerf. Sawing parameters which work for one material may not be optimal for other materials. Since compound devices, particularly image sensors are made of substrates of dissimilar materials, one set of sawing parameters, such as a particular speed of cut, saw rotation speed or pressure or one set of laser parameters such as pulse energy or repetition rate may be good for one substrate material but not the other. Glass, generally being more brittle than silicon wafers, has a tendency to chip or crack along the kerf when it is sawn or laser processed. In order to prevent chipping and cracking, the speed at which the diamond saw travels while sawing the glass substrate has to be much slower than when sawing silicon alone. This can also be true when laser processing. This has deleterious effects on system throughput. In addition, mechanical saws have a minimum width due to mechanical factors thereby establishing a minimum width for the streets that must contain the kerfs formed when sawn by mechanical saws. Typical minimum width for mechanical saw kerfs are about 100 micron. Since streets represent wasted space on substrates that could otherwise be used for active device elements, there is a desire to minimize the space devoted to streets and increase the space available for active device elements.

[0012] In accordance with the information presented above, there is therefore a continuing need for a method of singulating compound semiconductor devices that prevents chipping or cracking damage to the device, avoids adding extra chemicals, equipments and manufacturing steps to the singulation process and maintains system throughput when compared to prior art methods.

Summary of the Invention

[0013] One object of the instant invention is to provide a method for singulation of compound electronic devices. Another object of the instant invention is to provide a method for singulation of compound electronic devices that avoids creating cracks or chips while maintaining acceptable cutting speeds. A further object of the instant invention is to provide a method for singulation of compound electronic devices that

minimizes the size of streets. Compound electronic devices are particularly difficult to singulate due to their construction with two or more substrates requiring simultaneous separation to perform singulation. In particular, image sensor devices typically contain both active electronic device substrates such as silicon and transparent protective substrates made of glass or glass-like material, typically with differing thicknesses. One embodiment of the invention disclosed herein uses different separation techniques for different layers in the compound semiconductor device. In particular, at least one substrate is diced or laser machined to form a through-cut kerf while at least one other layer is scribed and subsequently mechanically cleaved.

[0014] In an embodiment of the instant invention, laser parameters are predetermined to improve the quality of the substrate following laser processing while maintaining acceptable throughput rates. Laser parameters can be adjusted to determine the rate and depth of cut for different materials and also determine the amount of undesirable cracking and chipping produced as a result of the laser processing. Some of the parameters that can be adjusted include wavelength, beam quality, temporal pulse width, temporal pulse shape, spatial pulse width, spatial pulse shape, pulse repetition frequency, polarization, pulse energy, laser spot size, laser spot position, and laser beam axis direction. Multiple laser beams may also be advantageously used to singulate compound electronic devices. These multiple beams can be derived from a single laser source or from two or more laser sources employing the same or different wavelengths.

[0015] Figs 6a, b, and c show schematically how an embodiment of the instant invention begins singulating compound electronic devices, a cross-sectional view of which is illustrated. In Fig 6a, a pulsed laser beam 80 with laser parameters set to first predetermined values is focused near the surface of first substrate 82. In this example first substrate 82 is a silicon wafer with image sensor electronics 85 on the front surface 84 of the wafer and wafer bumps one of which is indicated 86 to permit subsequent interconnection and packaging. The first substrate 82 is connected to the second substrate 90 by spacers, one of which is indicated 88 that space the second substrate 90 away from the substrate 82 and that form a seal that prevents contaminants from reaching circuitry 85 on the front surface 84 of the first substrate 82. The spacers 88 are arranged along the streets, one of which is indicated 92 of the first substrate 82 to permit

singulation while maintaining the aforementioned seal. Note that the laser beam 80 is focused directly above the street 92. In Fig 6b the laser beam 80 has begun to form a kerf 94 in the first substrate 82, while debris 96 is ejected from the kerf 94. In Fig 6c the laser beam 80 has machined completely through the first substrate 82, forming a through cut 98. Note that the debris 96 created by the machining process is contained to the area between spacers 88 containing the street 92, thereby preventing contamination of circuitry 85 on the front surface 84 of the substrate. The laser beam 80 is moved along the desired direction of the kerf by the laser processing system (not shown), thereby forming a through cut in the first substrate 82 along the area of the street 92.

[0016] Figs 7a and 7b show a schematic view of the second phase of compound electronic device singulation using pulsed laser beams. In Fig 7a, a pulsed laser beam 104 with laser parameters set to second predetermined values is directed through the machined kerf 98 in the first substrate 82 to impinge the second substrate 90 and form a scribe 100. Note that debris 102 from this machining step is contained by the spacers 88 in the area of the street 92 as above. Fig 7b shows the completed scribe 100 in second substrate 90. Setting the laser focal spot above the surface of the second substrate 90 and directing it through the machined kerf 98 in the first substrate 82 creates a peak in the spatial energy distribution of the laser beam 104 in the direction perpendicular to the kerf, which tends to form a sharp scribe 100 in the second substrate 90. As the laser beam 104 is moved along the path formed by the machined kerf 98 by the laser processing system (not shown) the scribe 100 in the second substrate 90 is extended along the area of the street 92, thereby scribing the second substrate 90.

[0017] Figs 8a and b illustrate the effect of directing a laser beam through the cut made in the first substrate. The laser beam is measured using a setup like Fig 6c, where the laser beam 80 passes through a cut 98 in a first substrate 82. The laser beam profile is measured as if it were impinging on the second substrate 90. The laser beam 80 has a wavelength of 523 nm; beam M^2 of 1.0, a 10 μm focal spot focused 400 μm above the second substrate 90. In this embodiment the first substrate 82 is between 70 and 180 μm thick with a 15 μm gap between the first substrate 82 and the second substrate 90. Fig 8a shows a graph 110 of a simulation of a profile of a laser beam 116 as it would appear on the surface of the second substrate 90 when directed through the first substrate 82 as

described, which plots irradiance in Watts/mm² 112 vs. distance from the optical axis in mm 114 measured in a direction perpendicular to the cut 98 in the first substrate 83. The profile in Fig 8a shows a sharp peak 118 in the distribution. This sharp peak 118 is formed as a result of diffraction and reflections in the laser beam as it passes through the cut 98 in the first substrate 82. Fig 8b shows a graph 120 of a simulation of the same laser beam 90 except measured parallel to the direction of the cut 98. This graph plots irradiance in Watts/mm² 122 vs. displacement from the optical axis of the laser beam in mm 124. Note that this distribution 126 of the laser beam irradiance follows a Gaussian distribution in contrast to the spiked distribution shown at 116. The sharp peaks on the pulse spatial distribution in the direction perpendicular to the direction of the cut cause the scribe formed in the glass to be narrower and more likely to cleave without cracks or chipping due to the increased melting close to the edge of the scribe. In addition, the defocused beam passing through the first substrate can melt debris and brittle materials such as low-k dielectrics on the edges of the kerf thereby making the kerf stronger and more resistant to cracking.

[0018] An embodiment of the instant invention uses picosecond (ps) or shorter laser pulses at high repetition rates to improve the quality of compound device singulation while maintaining system throughput by reducing stress fractures and cracks caused by laser processing. Fig 10 shows a glass substrate 140 following scribing with picosecond pulses. Note that the scribes 142 show little evidence of chipping and cracking as shown in Fig 3 (prior art). Fig 11 shows a cross sectional view of a glass substrate 150 showing a scribe 152 prior to cleaving. Note the relatively featureless heat affected zone 154, showing none of the void 56 or fractures 58 visible in Fig 4 (prior art). Fig 12 shows a side view of a substrate 160 following scribing with picosecond pulses and cleaving with the scribe 162 shown on the right hand side of the substrate 160. Note the absence of cracking in the glass substrate 160, contrasted with the cracks 60 evident in a similar view shown in Fig 5 (prior art). This absence of chipping or cracking in this cross section demonstrates that picosecond and shorter pulses can scribe glass and provide a crack-free cleave plane.

[0019] An embodiment of the instant invention uses picosecond or femtosecond duration laser pulses at selected energy levels to reduce the amount of chipping and cracking of

the substrates when machining. Fig 5 shows a substrate 70 following scribing with a picosecond laser pulses. Note the smooth edges of the scribe 72, showing little of the chipping or cracking associated with prior art nanosecond pulse scribing. These short duration pulses ablate or remove material from the workpiece without causing chipping or cracking because the duration of the pulse is shorter than the amount of time required for heat generated by the process to migrate from the location of the laser spot to the surrounding material and thereby create a heat affected zone (HAZ). In addition, the amount of energy per pulse is carefully set to be within a range of one to ten times the minimum amount of energy required to begin ablating the material, also called the ablation threshold. Energies of less than one times the ablation threshold for a given material will of course not ablate the material. Energies in excess of ten times the ablation threshold will ablate the material and in addition couple energy into the surrounding material creating a HAZ containing cracks and chips. Laser pulses of femtosecond or picosecond duration with per-pulse energies of between one and ten times the ablation threshold of a particular material will remove material within the focal spot of the laser beam with minimal heating effect on the surrounding material.

[0020] Following laser machining of the first and second substrates, Figs 9a and b illustrate schematically two ways to cleave the substrates following through cutting and scribing. Fig 9a shows the compound electronic device from Figs 6 and 7 following through cutting of the first substrate 82 forming a kerf 98 and following scribing the second substrate 90 forming a scribe 100. The substrates comprising the devices is attached to dicing tape 130, which is an adhesive tape typically mounted on a metal ring with an opening larger than the substrates. The dicing tape 130 is then stretched in a direction 132 perpendicular to the scribe 100 thereby causing the second substrate to cleave 134 starting with the scribe 100. Another embodiment of the instant invention show in Fig 9b uses a device (not shown) to apply upward pressure 135 on the bottom of the second substrate 90 directly underneath the scribe 100 as the tape is also stretched 132 perpendicular to the second substrate 90 to assist in the formation of the cleave 134. Fig 10 shows a side view of a substrate 140 scribed 142 and cleaved according to the instant invention. Note the lack of cracking and chipping, in contrast to the prior art side view shown in Fig 4b.

Brief Description of the Drawings

- [0021]** Fig 1. Top view of a schematic diagram of a semiconductor wafer.
- [0022]** Fig 2. Side view of compound electronic devices on a substrate.
- [0023]** Fig 3. Photograph of scribes formed by nanosecond pulses.
- [0024]** Fig 4. Cross-sectional photograph of scribes formed in a glass substrate by nanosecond pulses.
- [0025]** Fig 5. Side view photograph of a glass substrate following scribing by nanosecond pulses and cleaving.
- [0026]** Figs 6a, b, and c. Schematic diagrams showing steps in the singulation process of compound electronic devices according to an embodiment of the instant invention.
- [0027]** Figs 7a and b. Schematic diagrams showing further steps in the singulation process according to an embodiment of the instant invention.
- [0028]** Figs 8a and b. Graphs showing spatial irradiance distribution for laser pulses.
- [0029]** Figs 9a and b. Schematic diagrams showing substrate cleaving according to embodiments of the instant invention.
- [0030]** Fig 10. Photograph of scribes formed in a glass substrate by pulses according to an embodiment of the instant invention.
- [0031]** Fig 11. Cross-sectional photograph of a glass substrate scribe following scribing according to an embodiment of the instant invention.
- [0032]** Fig 12. Side view photograph of a glass substrate following scribing and cleaving according to an embodiment of the instant invention

Detailed Description of Preferred Embodiments

[0033] One object of the instant invention is to provide a method for singulation of compound electronic devices. Another object of the instant invention is to provide a method for singulation of compound electronic devices that avoids creating cracks or chips while maintaining acceptable cutting speeds. A further object of the instant

invention is to provide a method for singulation of compound electronic devices that minimizes the size of streets. Compound electronic devices are particularly difficult to singulate due to their construction with two or more substrates requiring simultaneous separation to perform singulation. In particular, image sensor devices typically contain both active electronic device substrates such as silicon and transparent protective substrates made of glass or glass-like material, typically with differing thicknesses. One embodiment of the invention disclosed herein uses different separation techniques for different layers in the compound semiconductor device. In particular, at least one substrate is diced or laser machined to form a through-cut kerf while at least one other layer is scribed and subsequently mechanically cleaved. An exemplary system that can be employed to perform the methods disclosed by the instant invention is the Cygnus 7000 Wafer Singulation System, manufactured by Electro Scientific Industries, Inc. Portland, OR. This system typically employs a fiber optic laser manufactured by Time Bandwidth, AB, Geneva, Switzerland which has an average power of 20 Watts and operates at a wavelength of 532 nm. Other lasers could also be used to perform this singulation as long as they could be adjusted to operate within the parameter ranges specified by the instant invention.

[0034] In an embodiment of the instant invention, laser parameters are predetermined to improve the quality of the substrate following laser processing while maintaining acceptable throughput rates. Laser parameters can be adjusted to determine the rate and depth of cut for different materials and also determine the amount of undesirable cracking and chipping produced as a result of the laser processing. Some of the parameters that can be adjusted include wavelength, beam quality, temporal pulse width, temporal pulse shape, spatial pulse width, spatial pulse shape, pulse repetition frequency, polarization, pulse energy, laser spot size, laser spot position, and laser beam axis direction. Multiple laser beams may also be advantageously used to singulate compound electronic devices. These multiple beams can be derived from a single laser source or from two or more laser sources employing the same or different wavelengths. A method for advantageously combining laser beams for a laser processing application is shown in U.S. patent application number 2006/0261051 Synthetic Pulse Repetition Rate Processing for Dual-

[0035] An example of a compound electronic device that could be singulated by the methods disclosed by the instant invention is a complementary metal-oxide semiconductor image sensor manufactured by Aptina Imaging as part number MT9M001C12STM. This sensor comprises an active sensor device with a glass protective cover and can be schematically represented as shown in Figs 6 and 7. Figs 6a, b, and c show schematically how an embodiment of the instant invention begins singulating compound electronic devices, a cross-sectional view of which is illustrated. In Fig 6a, a pulsed laser beam 80 with laser parameters set to first predetermined values is focused near the surface of first substrate 82. In this example first substrate 82 is a silicon wafer with image sensor electronics 85 on the front surface 84 of the wafer and wafer bumps one of which is indicated 86 to permit subsequent interconnection and packaging. The first substrate 82 is connected to the second substrate 90 by spacers, one of which is indicated 88 that space the second substrate 90 away from the substrate 82 and that form a seal that prevents contaminants from reaching circuitry 85 on the front surface 84 of the first substrate 82. The spacers 88 are arranged along the streets, one of which is indicated 92 of the first substrate 82 to permit singulation while maintaining the aforementioned seal. Note that the laser beam 80 is focused directly above the street 92. In this embodiment the laser beam is directed perpendicular to the surface of the substrate, although other angles may be used advantageously to produce differently shaped kerfs if desired.

[0036] Laser parameters for this step include a pulse width between about 100 fs and 1 ns, particularly between about 1 ps and 1 ns, and more particularly about 100 ps. The laser wavelength is between about 255 um and 10 um, particularly between about 255 um and 1.0 um, and more particularly about 532 nm. The laser beam is focused to form a focal spot at or near the front surface 84 of the first substrate 82 of between about 1 um and 100 um, particularly between about 1 um and 20 um, more particularly about 10 um. Pulse repetition frequency for this step is between about 100 kHz and 10 MHz, particularly between about 100 kHz and 1 MHz and more particularly about 100 kHz. Pulse energy is preferentially between 1 nanoJoule and 1 milliJoule, particularly between

about 1 nanoJoule and 1 microJoule, more particularly about 100 nanoJoules. Beam quality for this step is an M^2 of between about 1.0 and 1.5, more particularly of about 1.0. **[0037]** Spatial pulse shape for this step is approximately Gaussian, although other shapes may be used advantageously. For example, a square spatial distribution, formed by a combination of optical components such as apertures and filters, could be used to change the shape of the kerf walls without slowing the process or creating chips or cracks. This is also true of polarization. Circular polarization will cause machining to occur evenly in all directions from the central axis of the laser beam, while linearly polarized laser beams preferentially ablate material along the direction parallel with the polarization. Radial polarization can result in smaller spot sizes for a given wavelength. Temporal pulse shape is approximately Gaussian, although other shapes may be used. Pulses as emitted from laser resonators typically have Gaussian temporal profiles but these profiles can be modified by available optical means to have pulses which range from square to more complex tailored shapes. Production of tailored pulses in particular is disclosed in U.S. patent 7,126,746 Generating Sets of Tailored Pulses (Sun, et. al.), assigned to the assignee of the instant invention, included herein by reference. The laser spot shape can also be altered to produce other shapes. For example, the spatial distribution can be made elliptical or rectangular using standard optical components such as apertures and lenses. In addition, holographic optical elements may be used to form the beam into a variety of useful shapes, including a “top hat” configuration, a “ring” configuration or other shapes. Descriptions of holographic or diffractive optical elements used in laser micromachining applications are found in U.S. patents 6,433,301 Beam Shaping and Projection Imaging with Solid State UV Gaussian Beam to Form Vias (Dunsky, et. al.) and U.S. patent 6,791,060 Beam Shaping and Projection Imaging with Solid State UV Gaussian Beam to Form Vias (Dunsky, et. al.), both assigned to the assignee of the instant invention and included herein by reference.

[0038] In an embodiment of the instant invention the kerfs or scribes formed in the substrates are typically straight lines, although curves and other shapes may be used advantageously in some instances. Furthermore the laser beam can be directed to move with respect to the workpiece in such a fashion as to deliver pulses at a rate that can dice or through-cut a substrate in one pass, i.e. the laser beam moves along a path on substrate

from one point to another without reversing direction or otherwise machining the same point more than once, relying on the laser pulses to completely machine through the substrate before moving on to the next position. More typically the laser beam is directed to machine the workpiece in more than one pass, where the laser beam is directed to each point along the kerf or scribe more than once, each pass removing more material in depth until the desired depth or through-cut is achieved.

[0039] In Fig 6b the laser beam 80 has begun to form a kerf 94 in the first substrate 82, while debris 96 is ejected from the kerf 94. In Fig 6c the laser beam 80 has machined completely through the first substrate 82, forming a through cut 98. Note that the debris 96 created by the machining process is contained to the area between spacers 88 containing the street 92, thereby preventing contamination of circuitry 85 on the front surface 84 of the substrate. The laser beam 80 is moved along the desired direction of the kerf by the laser processing system (not shown), thereby forming a through cut in the first substrate 82 along the area of the street 92.

[0040] Figs 7a and 7b show a schematic view of the second phase of compound electronic device singulation using pulsed laser beams. In Fig 7a, a pulsed laser beam 104 with laser parameters set to second predetermined values is directed through the machined kerf 98 in the first substrate 82 to impinge the second substrate 90 and form a scribe 100. Note that debris 102 from this machining step is contained by the spacers 88 in the area of the street 92 as above. Fig 7b shows the completed scribe 100 in second substrate 90. Setting the laser focal spot above the surface of the second substrate 90 and directing it through the machined kerf 98 in the first substrate 82 creates a peak in the spatial energy distribution of the laser beam 104 in the direction perpendicular to the kerf, which tends to form a sharp scribe 100 in the second substrate 90. As the laser beam 104 is moved along the path formed by the machined kerf 98 by the laser processing system (not shown) the scribe 100 in the second substrate 90 is extended along the area of the street 92, thereby scribing the second substrate 90.

[0041] Laser parameters for the second phase of this embodiment can be the same as the first phase except that the laser spot is focused above the surface to be scribed. The laser spot is focused to a point between about 100 μm above the surface to about 1000 μm above the surface. More particularly the spot is focused to a point about 400 μm above

the surface to be scribed. This has the effect of defocusing the laser beam at the surface of the workpiece, thereby reducing the laser irradiance at any given point on the surface and thereby reducing the tendency of the material to crack due to excessive energy. In addition the defocused beam tends to melt debris on the surface thereby decreasing the likelihood of loose material or sharp edges, both of which are undesirable. In addition, focusing the laser beam through the kerf previously machined in the first substrate 82 causes the beam to shape and refocus advantageously.

[0042] Figs 8a and b illustrate the effect of directing a laser beam through the cut made in the first substrate. The laser beam is measured using a setup like Fig 6c, where the laser beam 80 passes through a cut 98 in a first substrate 82. The laser beam profile is measured as if it were impinging on the second substrate 90. The laser beam 80 has a wavelength of 523 nm; beam M^2 of 1.0, a 10 μm focal spot focused 400 μm above the second substrate 90. In this embodiment the first substrate 82 is between 70 and 180 μm thick with a 15 μm gap between the first substrate 82 and the second substrate 90. Fig 8a shows a graph 110 of a simulation of a profile of a laser beam 116 as it would appear on the surface of the second substrate 90 when directed through the first substrate 82 as described, which plots irradiance in Watts/mm^2 112 vs. distance from the optical axis in mm 114 measured in a direction perpendicular to the cut 98 in the first substrate 83. The profile in Fig 8a shows a sharp peak 118 in the distribution. This sharp peak 118 is formed as a result of diffraction and reflections in the laser beam as it passes through the cut 98 in the first substrate 82. Fig 8b shows a graph 120 of a simulation of the same laser beam 90 except measured parallel to the direction of the cut 98. This graph plots irradiance in Watts/mm^2 122 vs. displacement from the optical axis of the laser beam in mm 124. Note that this distribution 126 of the laser beam irradiance follows a Gaussian distribution in contrast to the spiked distribution shown at 116. The sharp peaks on the pulse spatial distribution in the direction perpendicular to the direction of the cut cause the scribe formed in the glass to be narrower and more likely to cleave without cracks or chipping due to the increased melting close to the edge of the scribe. In addition, the defocused beam passing through the first substrate can melt debris and brittle materials such as low-k dielectrics on the edges of the kerf thereby making the kerf stronger and more resistant to cracking.

[0043] An embodiment of the instant invention uses picosecond or shorter laser pulses at high repetition rates to improve the quality of compound device singulation while maintaining system throughput by reducing stress fractures and cracks caused by laser processing. Fig 10 shows a glass substrate 140 following scribing with picosecond pulses. Note that the scribes 142 show little evidence of chipping and cracking as shown in Fig 3 (prior art). Fig 11 shows a cross sectional view of a glass substrate 150 showing a scribe 152 prior to cleaving. Note the relatively featureless heat affected zone 154, showing none of the void 56 or fractures 58 visible in Fig 4 (prior art). Fig 12 shows a side view of a substrate 160 following scribing with picosecond pulses and cleaving with the scribe 162 shown on the right hand side of the substrate 160. Note the absence of cracking in the glass substrate 160, contrasted with the cracks 60 evident in a similar view shown in Fig 5 (prior art). This absence of chipping or cracking in this cross section demonstrates that picosecond and shorter pulses can scribe glass and provide a crack-free cleave plane.

[0044] In particular, an embodiment of the instant invention employs laser pulses with temporal pulse widths in the picosecond or femtosecond range to minimize chipping and cracking in the substrates being processed. Fig 5 shows a substrate 70 following scribing with a picosecond laser pulses. Note the smooth edges of the scribe 72, showing none of the chipping or cracking associated with prior art nanosecond pulse scribing. These short duration pulses ablate or remove material from the workpiece without causing chipping or cracking because the duration of the pulse is shorter than the amount of time required for heat generated by the process to migrate from the location of the laser spot to the surrounding material and thereby create a heat affected zone (HAZ). In addition, the amount of energy per pulse is carefully set to be within a range of one to ten times the minimum amount of energy required to begin ablating the material, also called the ablation threshold. Energies of less than one times the ablation threshold for a given material will of course not ablate the material. Energies in excess of ten times the ablation threshold will ablate the material and in addition couple energy into the surrounding material creating a HAZ containing cracks and chips. Laser pulses of femtosecond or picosecond duration with per-pulse energies of between one and ten

[0045] Following laser machining of the first and second substrates, Figs 9a and b illustrate schematically two ways to cleave the substrates following through cutting and scribing. Fig 9a shows the compound electronic device from Figs 6 and 7 following through cutting of the first substrate 82 forming a kerf 98 and following scribing the second substrate 90 forming a scribe 100. The substrates comprising the devices is attached to dicing tape 130, which is an adhesive tape typically mounted on a metal ring with an opening larger than the substrates. The dicing tape 130 is then stretched in a direction 132 perpendicular to the scribe 100 thereby causing the second substrate to cleave 134 starting with the scribe 100. Another embodiment of the instant invention show in Fig 9b uses a device (not shown) to apply upward pressure 135 on the bottom of the second substrate 90 directly underneath the scribe 100 as the tape is also stretched 132 perpendicular to the second substrate 90 to assist in the formation of the cleave 134. Fig 10 shows a side view of a substrate 140 scribed 142 and cleaved according to the instant invention. Note the lack of cracking and chipping, in contrast to the prior art side view shown in Fig 4b.

[0046] It will be apparent to those of ordinary skill in the art that many changes may be made to the details of the above-described embodiments of this invention without departing from the underlying principles thereof. The scope of the present invention should, therefore, be determined only by the following claims.

We claim:

1. An improved method for singulation of compound electronic devices using a laser processing system, wherein a plurality of said compound electronic devices are manufactured in an assembly that includes a first substrate and a second substrate arranged in layers, said plurality of said compound electronic devices being arranged so as to provide streets between said compound electronic devices, and said laser processing system having a laser beam comprising parameters including focal spot, speed, wavelength, energy, spot size, spot shape, pulse width, pulse shape and pulse repetition rate, said laser beam operative to laser machine said assemblies, the improvement comprising:

laser machining a through cut in said first substrate with said laser beam having first predetermined laser parameter values, said through cut coincident with one of said streets between said compound semiconductor devices; and

laser machining a scribe in said second substrate with said laser beam having second predetermined laser parameter values, said scribe in said second substrate being aligned with said through cut in said first substrate; and

singulating said compound electronic devices by mechanically cleaving said second substrate along said scribe.

2. The method of claim 1 wherein said laser parameters used to perform said laser machining of said first substrate include a wavelength between about 266 nm and 1064 nm, a total power between about 4 W and 12 W, a spot size between about 10 microns and 50 microns, a pulse repetition rate between about 100 KHz and 1 MHz, a pulse width between about 1 femtosecond and 1 nanosecond.

3. The method of claim 1 wherein said laser parameters used to perform said laser machining of said first substrate include a wavelength between about 266 nm and 1064

nm, a total power between about 4 W and 12 W, a spot size between about 10 microns and 50 microns, a pulse repetition rate between about 100 KHz and 1 MHz, a pulse width between about 1 femtosecond and 1 nanosecond.

4. The method of claim 1 wherein said focal spot of said laser beam is focused at about said top surface of said first substrate to perform said laser machining of said through cut in said first substrate.

5. The method of claim 1 wherein said focal spot of said laser beam is focused between about 100 microns and 1000 microns above said top surface of said first substrate to perform said laser machining of said scribe in said second substrate.

6. The method of claim 1 wherein said through cut in said first substrate is laser machined by making between 2 and 10 passes of said laser beam on said first substrate.

7. The method of claim 1 wherein said travel speed of said laser beam is between about 100 and 500 mm/s while performing said laser machining of said first substrate.

8. The method of claim 1 wherein said through cut in said second substrate is laser machined by making between 2 and 10 passes of said laser beam on said second substrate.

9. The method of claim 1 wherein said travel speed of said laser beam is between about 200 and 600 mm/s while performing said laser machining of said second substrate.

1/11

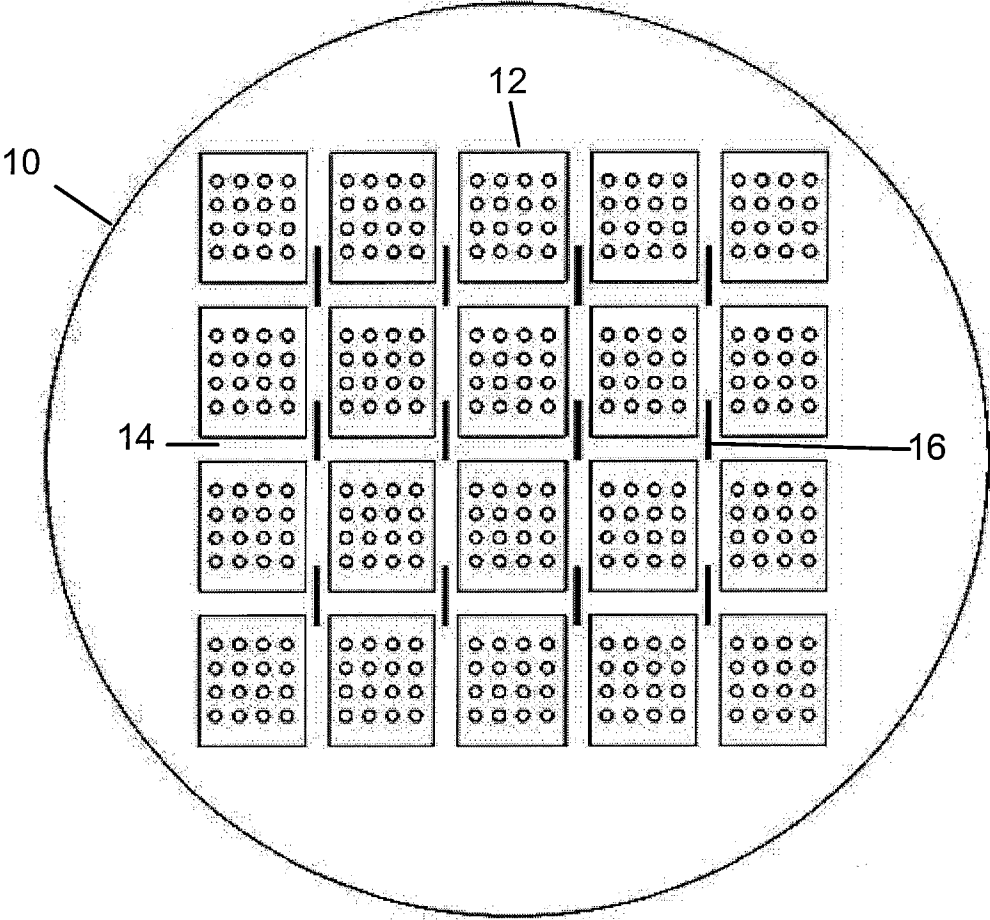


Fig 1
Prior Art

2/11

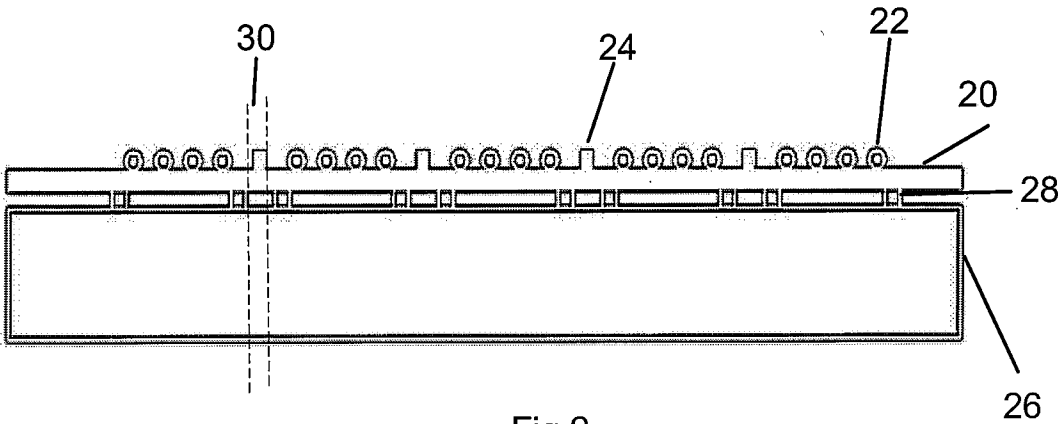


Fig 2
Prior Art

3/11

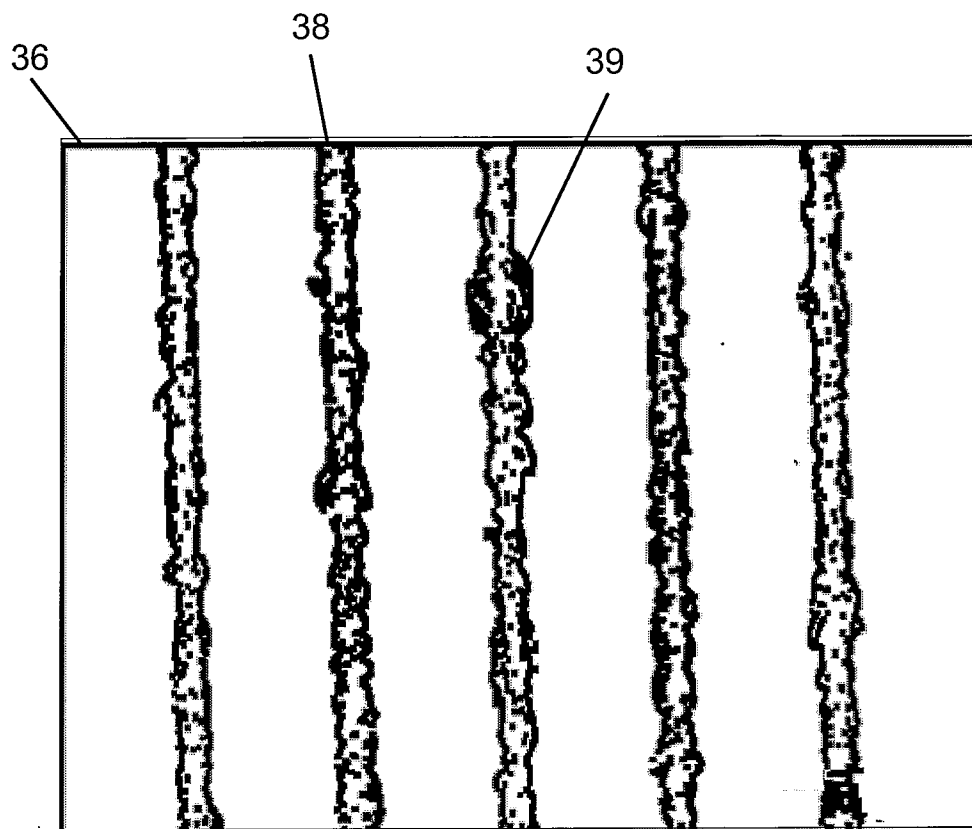


Fig 3
Prior Art

4/11

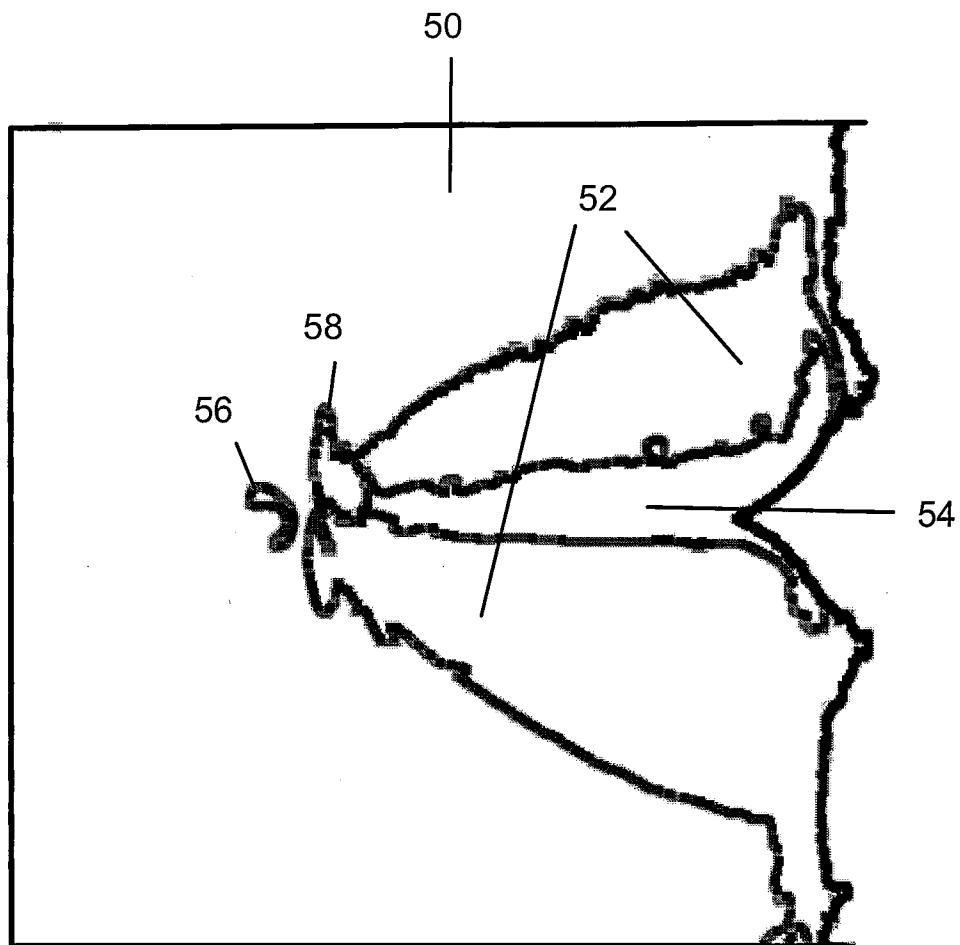


Fig 4
Prior Art

5/11

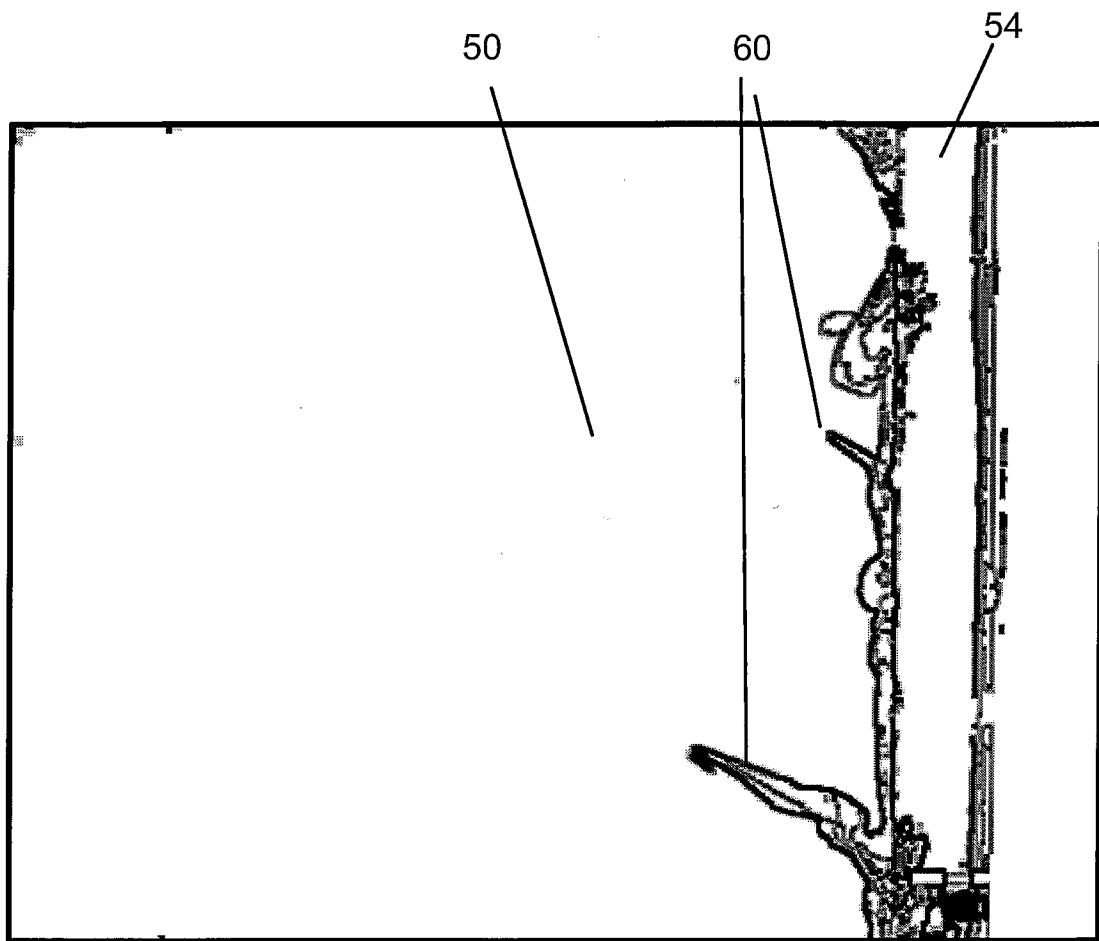


Fig 5
Prior Art

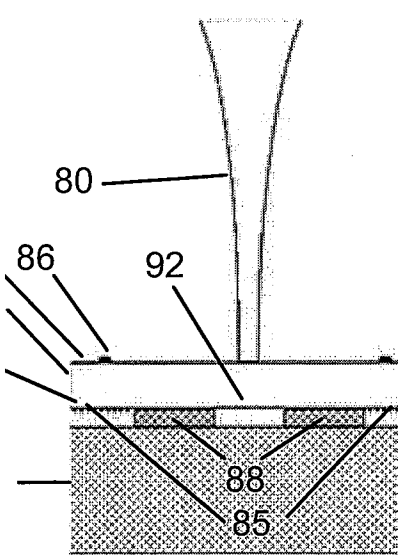


Fig 6a

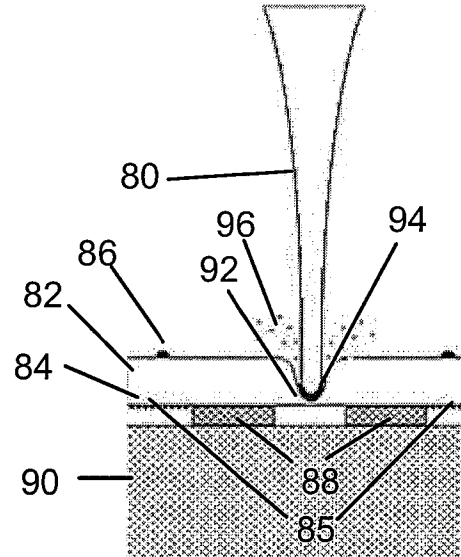


Fig 6b

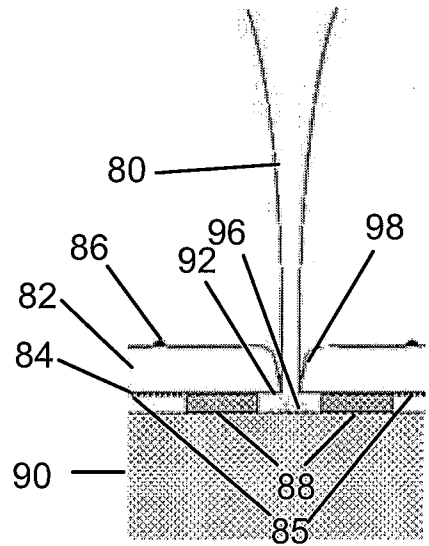


Fig 6c

7/11

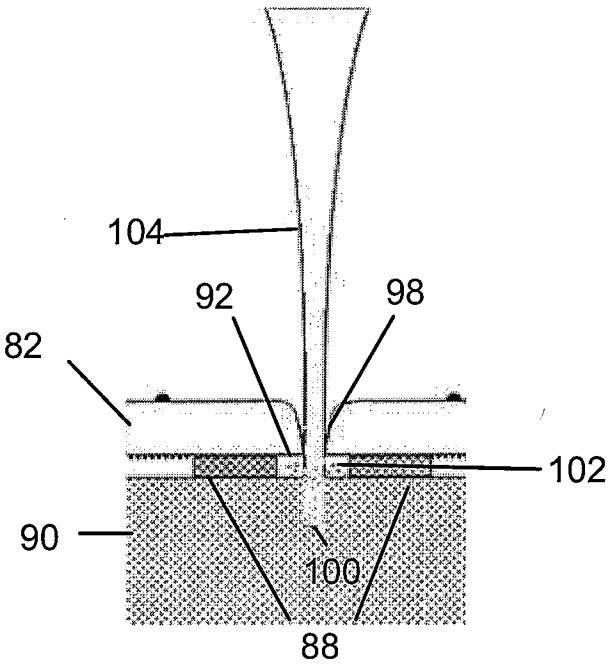


Fig 7a

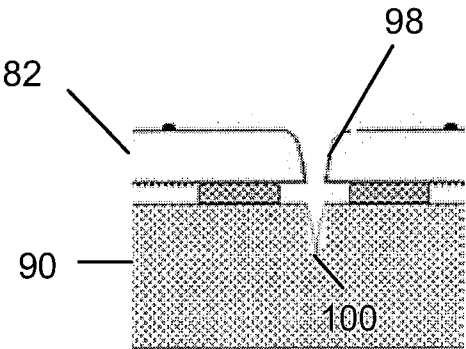


Fig 7b

8/11

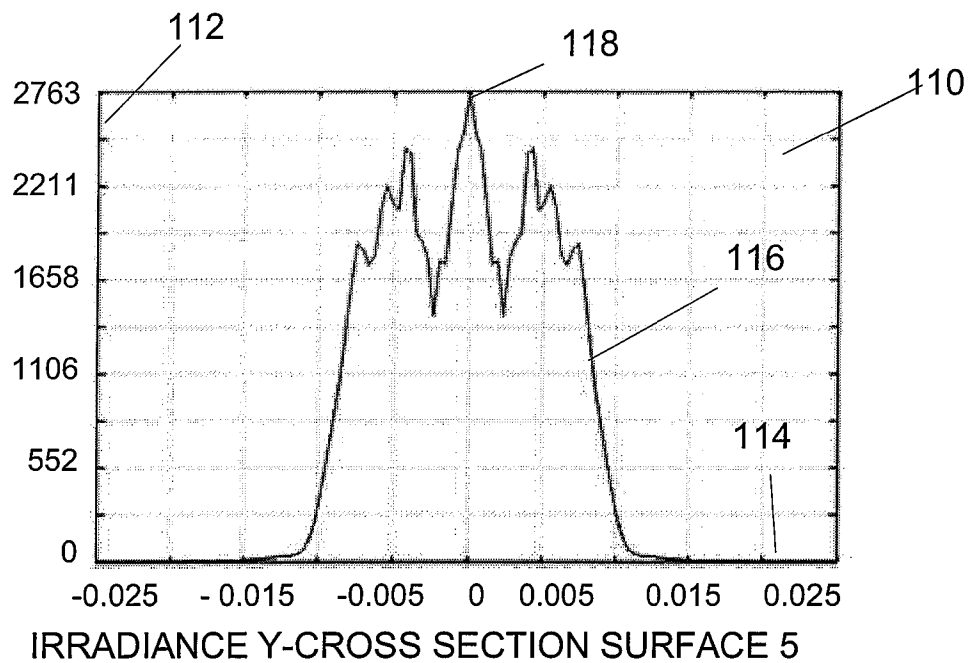


Fig 8a

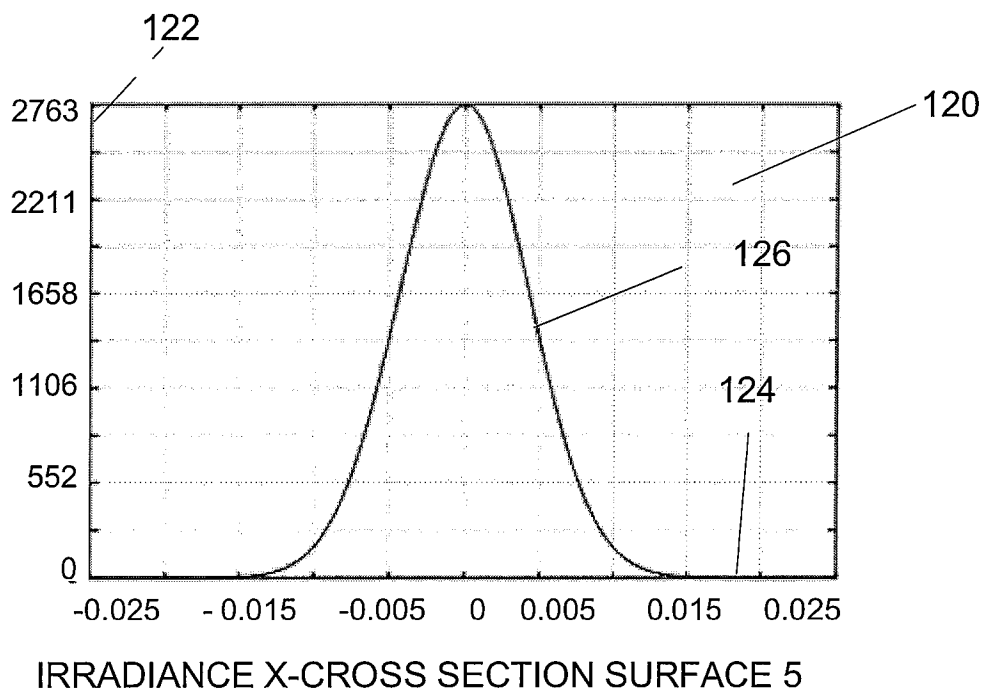


Fig 8b

9/11

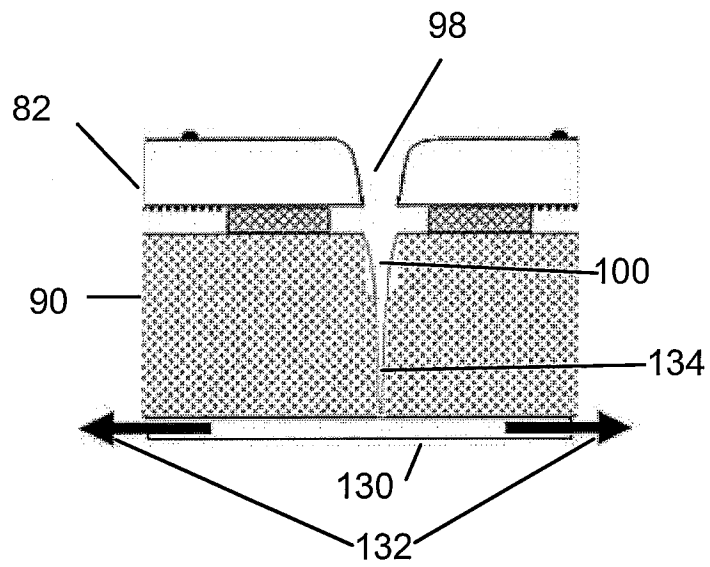


Fig 9a

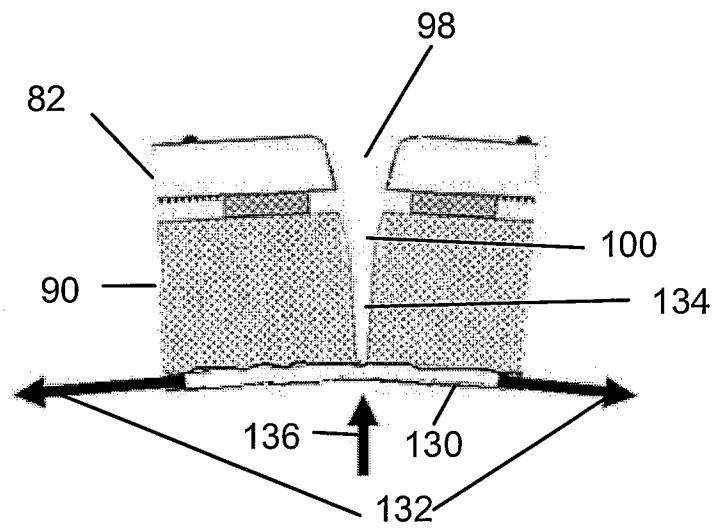


Fig 9b

10/11

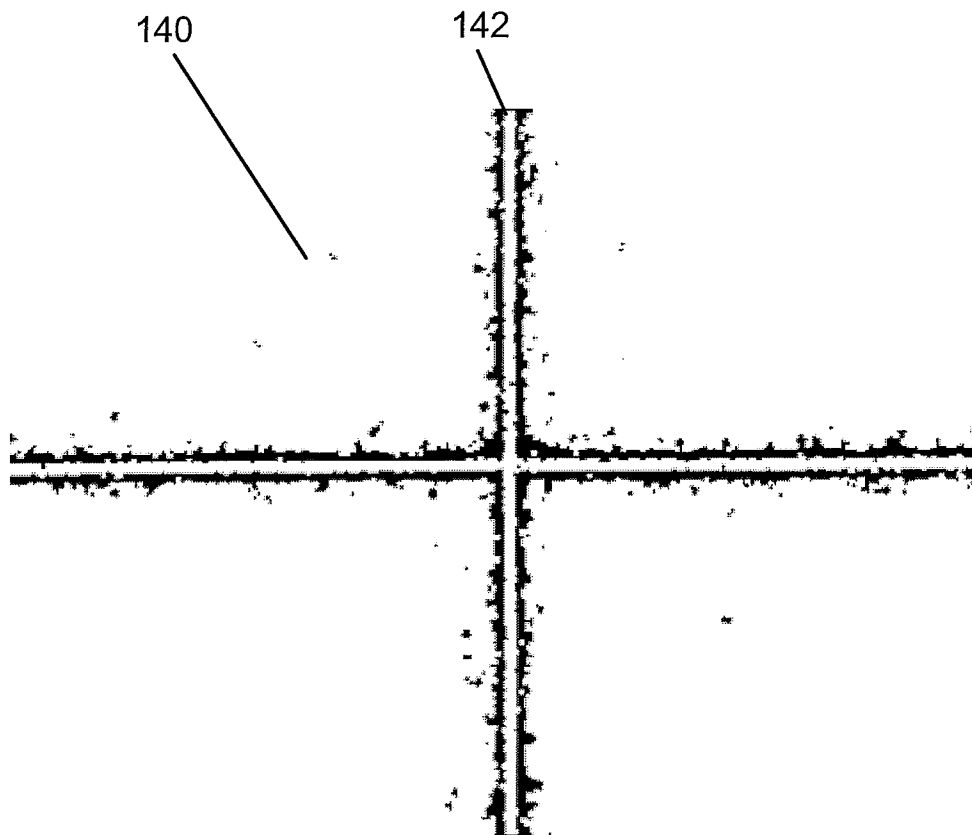


Fig 10

11/11

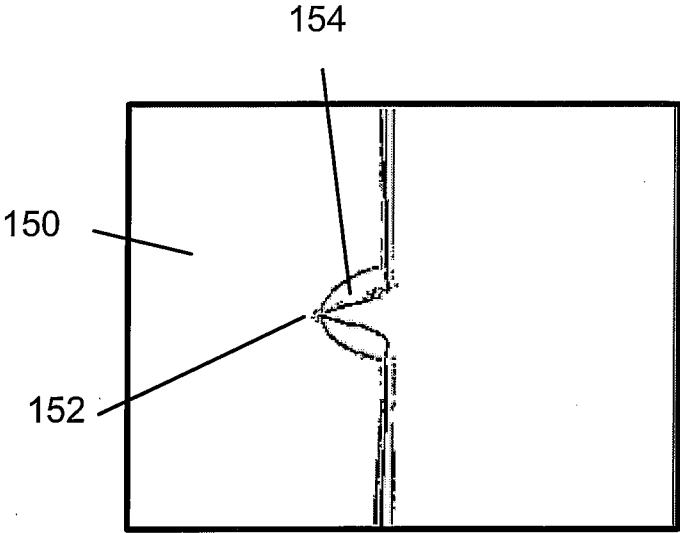


Fig 11

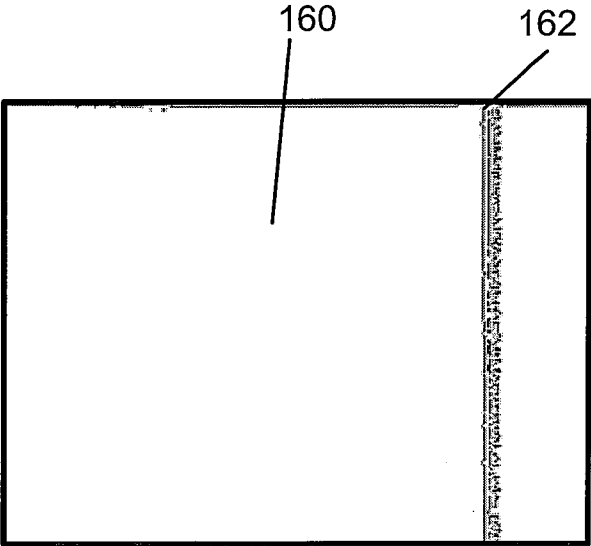


Fig 12